Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	2	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	2.5	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	-	MAX.	10	mA
V_{GT}		-	MAX.	1.3	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	-	MIN.	0.15	V
I_L	I_G =1.2I_{GT}				
dV/dt	V_D=540V Gate Open T_j =125		MIN.	10031.32 re f 495.84 558.48 0.	

FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

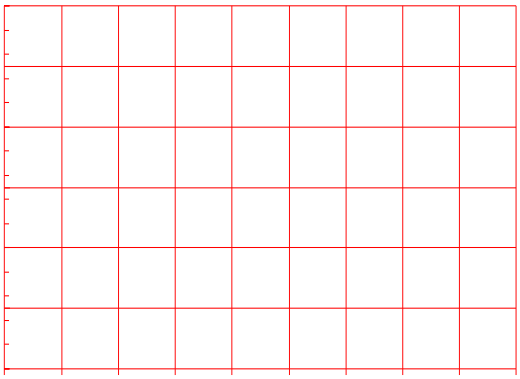
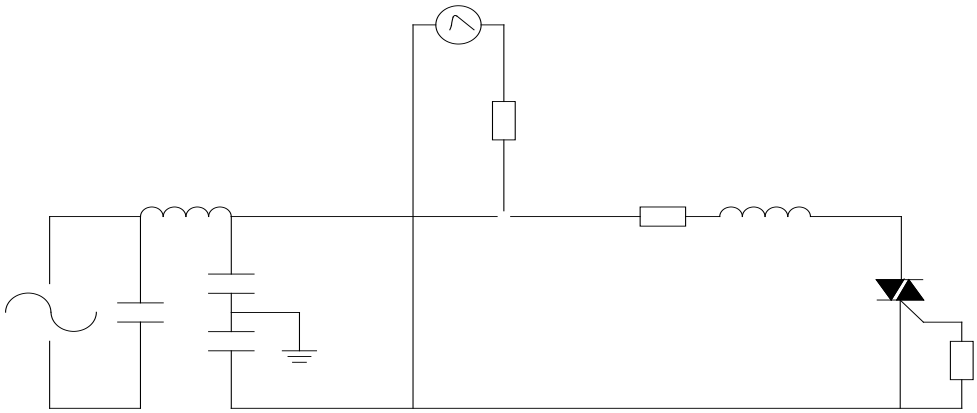
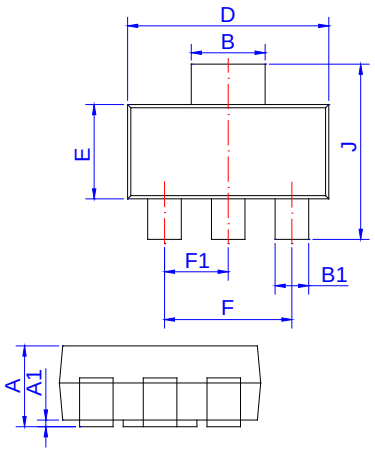


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JPTT01V-800SW	800	10	SOT-223	4,000	Tape & Reel



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.50	1.60	1.80	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	2.90	3.00	3.10	0.114	0.118	0.122
B1	0.60	0.70	0.80	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
E	3.30	3.50	3.70	0.130	0.138	0.146
F	4.40			0.173		
F1	2.20			0.087		
G	0.50		1.00	0.020		0.039
H	1.50	1.75	2.00	0.059	0.069	0.079
J	6.70	7.00	7.30	0.264	0.276	0.287
K						

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.
Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.
is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.
Copyright © 2025 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.